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CoolMOS™ Power Transistor

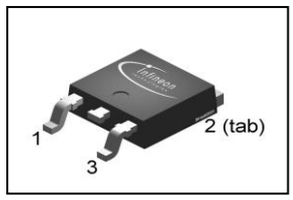
Features

- New revolutionary high voltage technology
- Extreme dv/dt rated
- High peak current capability
- Qualified according to AEC Q101
- Green package (RoHS compliant), Pb-free lead plating, halogen free for mold compound
- Ultra low gate charge
- Ultra low effective capacitances

Product Summary

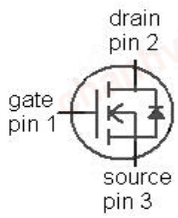
V_{DS}	800	V
$R_{DS(on)max}$ @ T_j = 25°C	2.7	Ω
$Q_{g,typ}$	12	nC

PG-TO252-3



CoolMOS™ 800V designed for:

- Automotive application with high DC bulk voltage
- Switching Application (i.e. active clamp forward)



Type	Package	Marking
IPD80R2k7C3A	PG-TO252-3	80C2k7A

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_C=25 °C	2	A
		T_C=100 °C	1.2	
Pulsed drain current[2]	$I_{D,pulse}$	T_C=25 °C	6	
Avalanche energy, single pulse	E_{AS}	I_D=1 A, V_{DD}=50 V	90	mJ
Avalanche energy, repetitive t_{AR}[2),3)]	E_{AR}	I_D=2 A, V_{DD}=50 V	0.05	
Avalanche current, repetitive t_{AR}[2),3)]	I_{AR}		2	A
MOSFET dv/dt ruggedness	dv/dt	V_{DS}=0…640 V	50	V/ns
Gate source voltage	V_{GS}	static	±20	V
		AC (f>1 Hz)	±30	
Power dissipation	P_{tot}	T_C=25 °C	42	W
Operating, Storage temperature	$Tj, Tstg$		-40 ... 150	°C

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Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	I_S	T_C=25 °C	2	A
Diode pulse current[2]	$I_{S,pulse}$		6	
Reverse diode dv/dt[4]	dv/dt		4	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	3	K/W
Thermal resistance, junction - ambient	R_{thJA}	SMD version, device on PCB, minimal footprint	-	-	62	
		SMD version, device on PCB, 6 cm^2 cooling area[5]	-	35	-	
Soldering temperature, reflow soldering	T_{sold}	reflow MSL1	-	-	260	°C

Electrical characteristics, at T_j=25 °C, unless otherwise specified

Static characteristics						
Drain-source breakdown voltage[1]	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=250 µA	800	-	-	V
Avalanche breakdown voltage	$V_{(BR)DS}$	V_{GS}=0 V, I_D=2 A	-	870	-	
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=0.12 mA	2.1	3	3.9	
Zero gate voltage drain current	I_{DSS}	V_{DS}=800 V, V_{GS}=0 V, T_j=25 °C	-	-	5	µA
		V_{DS}=800 V, V_{GS}=0 V, T_j=150 °C	-	25	-	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=1.2 A, T_j=25 °C	-	2.4	2.7	Ω
		V_{GS}=10 V, I_D=1.2 A, T_j=150 °C	-	5.5	-	
Gate resistance	R_G	f=1 MHz, open drain	-	1.2	-	Ω

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Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=100 V, f=1 MHz	-	290	-	pF
Output capacitance	C_{oss}		-	13	-	
Effective output capacitance, energy related[6)]	$C_{o(er)}$	V_{GS}=0 V, V_{DS}=0 V to 480 V	-	11	-	
Effective output capacitance, time related[7)]	$C_{o(tr)}$		-	26	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=400 V, V_{GS}=0/10 V, I_D=2 A, $R_{G,ext}$=47 Ω, Tj=25 °C	-	25	-	ns
Rise time	t_r		-	15	-	
Turn-off delay time	$t_{d(off)}$		-	72	-	
Fall time	t_f		-	18	-	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=640 V, I_D=2 A, V_{GS}=0 to 10 V	-	1.5	-	nC
Gate to drain charge	Q_{gd}		-	6	-	
Gate charge total	Q_g		-	12	16	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V
Reverse Diode						
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=I_S=2 A, T_j=25 °C	-	1	1.2	V
Reverse recovery time	t_{rr}	V_R=400 V, I_F=I_S=2 A, di_F/dt=100 A/µs	-	520	-	ns
Reverse recovery charge	Q_{rr}		-	2	-	µC
Peak reverse recovery current	I_{rrm}		-	6	-	A

[1)] For applications with applied blocking voltage > 65% of the specified blocking voltage, we recommend to evaluate the impact of the cosmic radiation effect in early design phase. For assessment please contact local Infineon sales office.

[2)] Pulse width t_p limited by $T_{j,max}$

[3)] Repetitive avalanche causes additional power losses that can be calculated as P_{AV}=E_{AR}*f.

[4)] I_{SD}≤I_D, di/dt≤400A/µs, V_{DClink} = 400V, V_{peak}<$V_{(BR)DSS}$, T_j<T_{jmax}, identical low side and high side switch

[5)] Device on 40mm*40mm*1.5 epoxy PCB FR4 with 6cm² (one layer, 70µm thick) copper area for drain connection. PCB is vertical without blown air

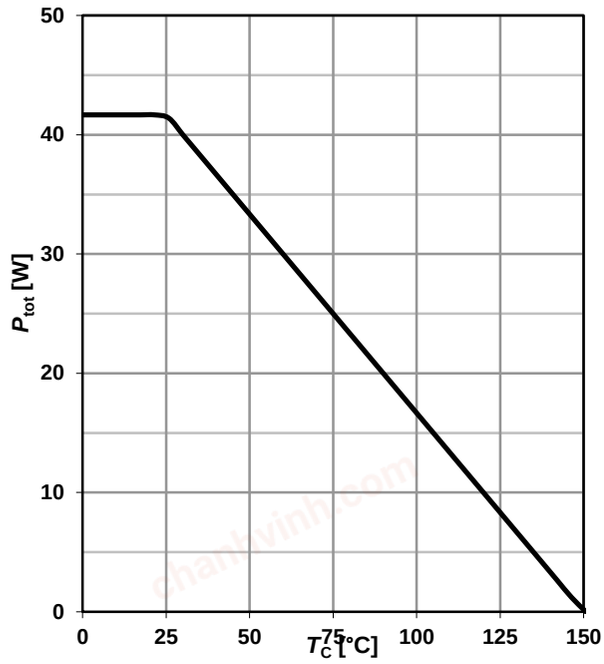
[6)] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

[7)] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

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1 Power dissipation

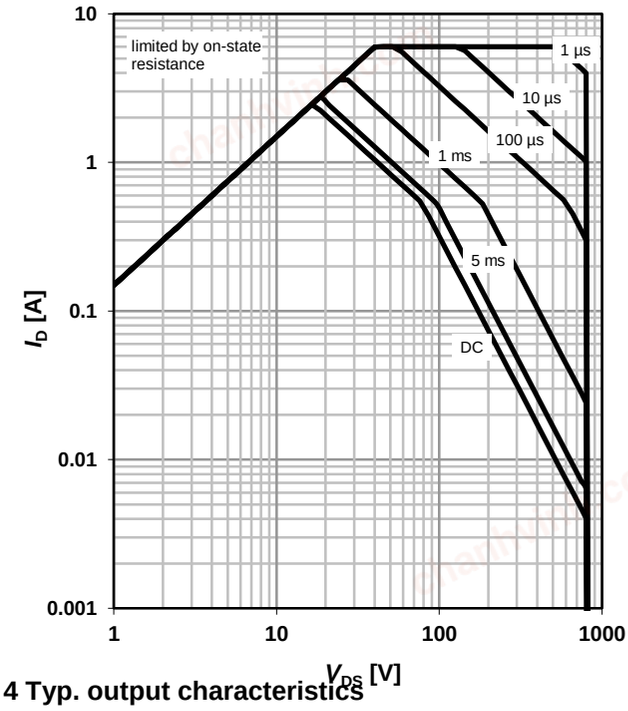
$P_{tot}=f(T_C)$



2 Safe operating area [1)]

$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$, Parameter: tp

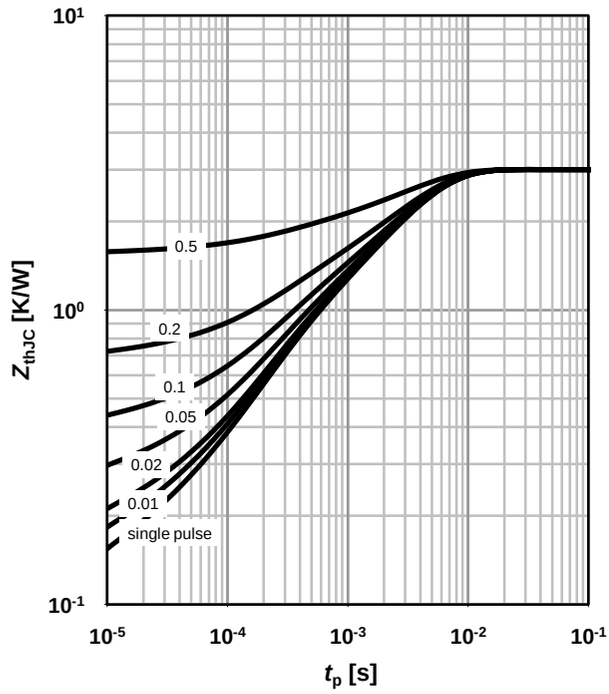
[1)] DC curve indicates operation at thermal equilibrated state, not guaranteed over lifetime.



3 Max. transient thermal impedance

$Z_{thJC}=f(t_P)$

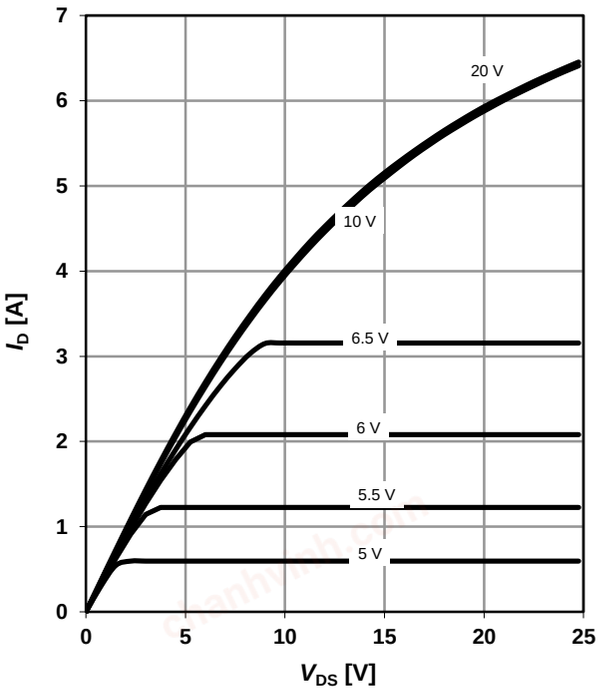
parameter: $D=t_p/T$



4 Typ. output characteristics

$I_D=f(V_{DS})$; $T_j=25$ °C; $t_p=10$ µs

parameter: V_{GS}

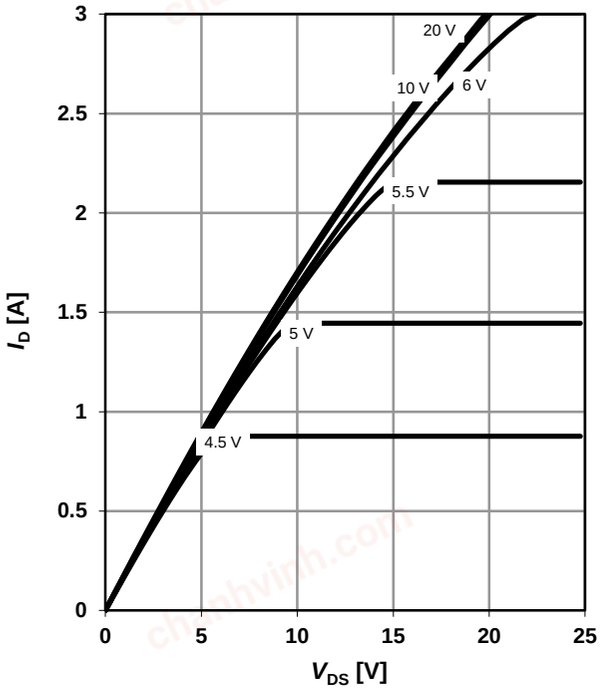


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5 Typ. output characteristics

$I_D=f(V_{DS})$; $T_j=150$ °C; $t_p=10$ µs

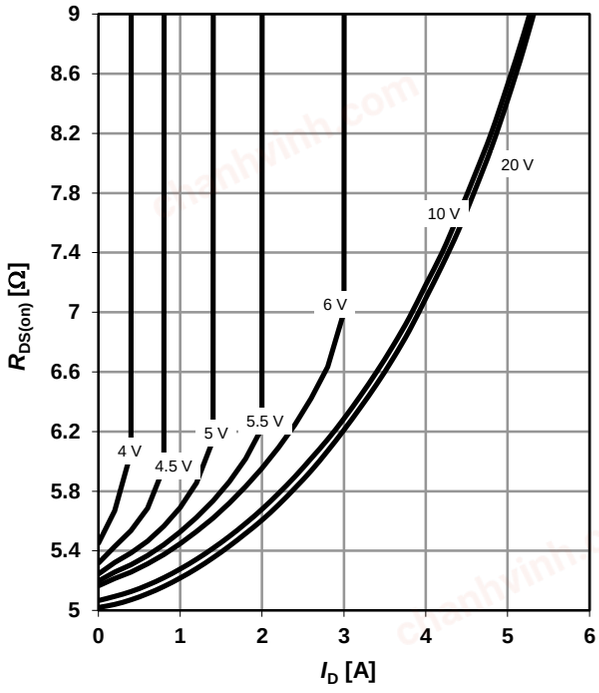
parameter: V_{GS}



6 Typ. drain-source on-state resistance

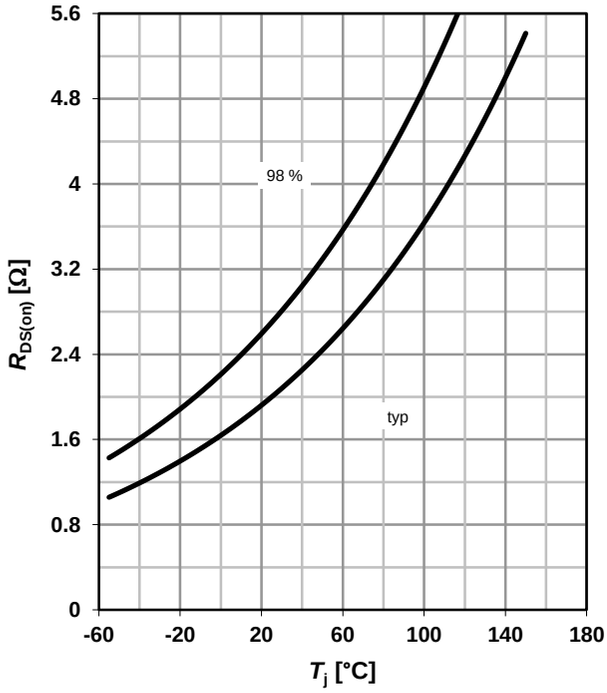
$R_{DS(on)}=f(I_D)$; $T_j=150$ °C

parameter: V_{GS}



7 Drain-source on-state resistance

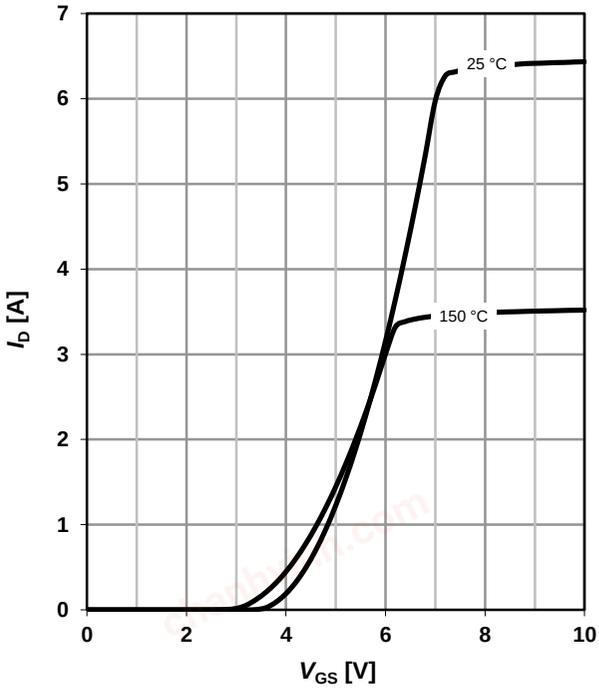
$R_{DS(on)}=f(T_j)$; $I_D=1.2$ A; $V_{GS}=10$ V



8 Typ. transfer characteristics

$I_D=f(V_{GS})$; $|V_{DS}|>2|I_D|R_{DS(on)max}$; $t_p=10$ µs

parameter: T_j

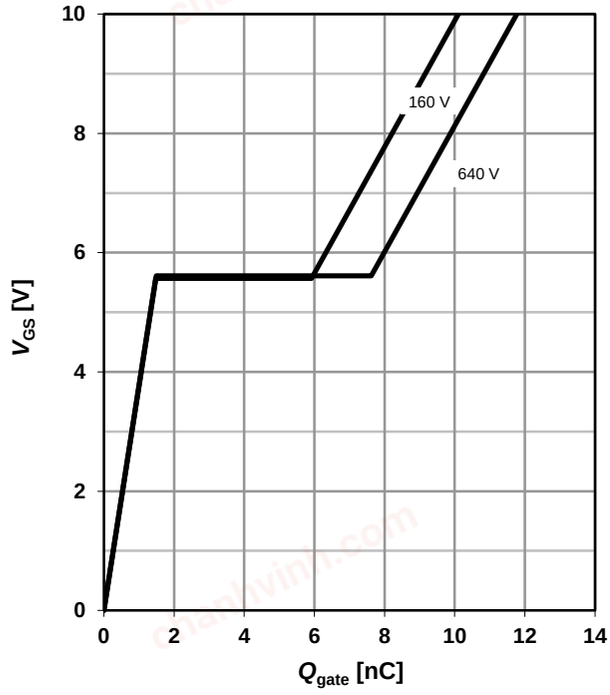


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9 Typ. gate charge

V_{GS}=f(Q_{gate}); I_D=2 A pulsed

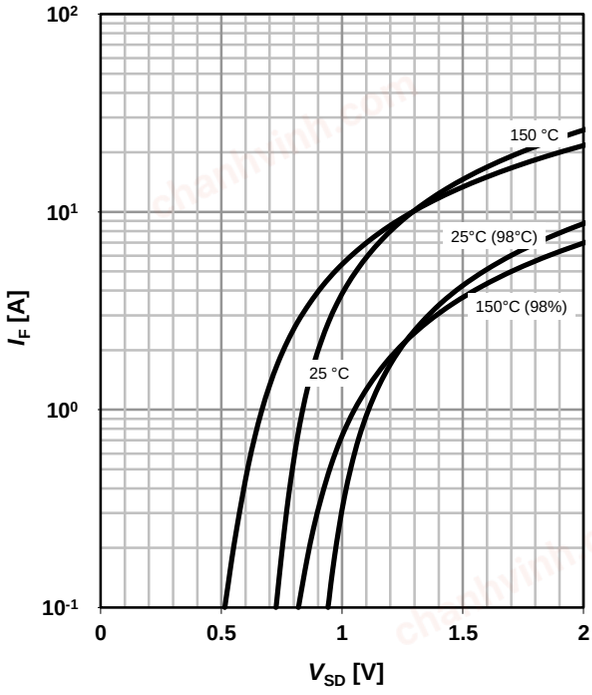
parameter: V_{DD}



10 Forward characteristics of reverse diode

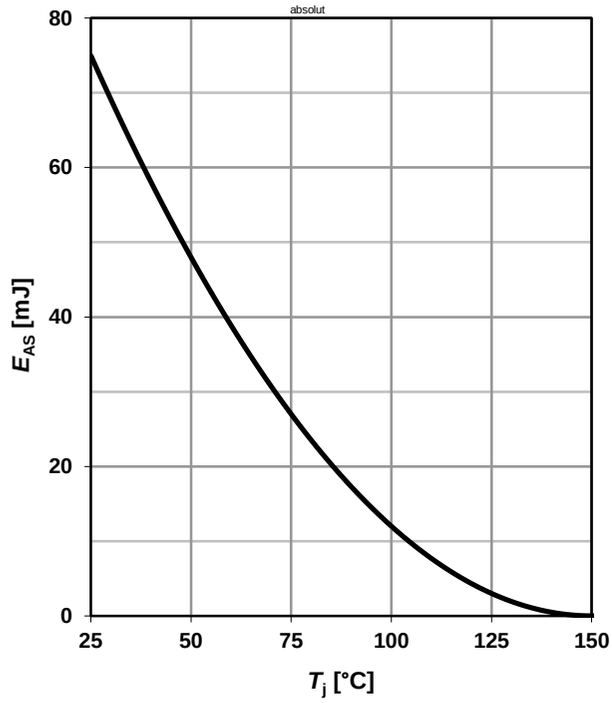
I_F=f(V_{SD}); t_p=10 µs

parameter: T_j



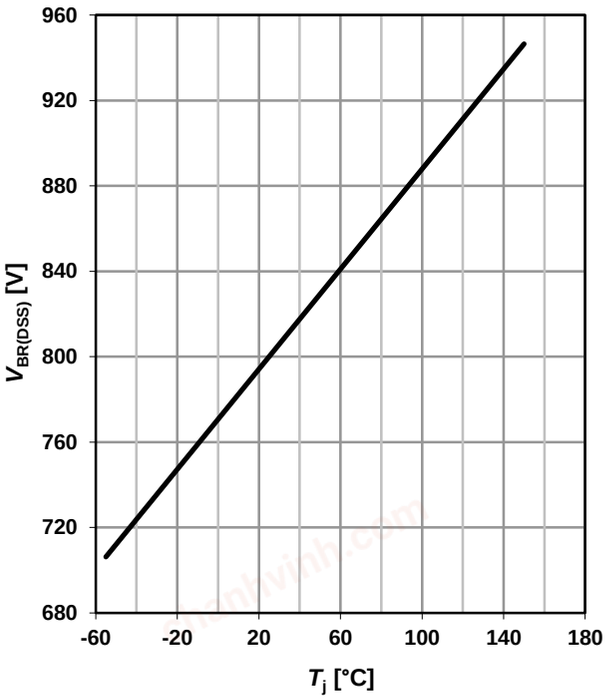
11 Avalanche energy

E_{AS}=f(T_j); I_D=1 A; V_{DD}=50 V



12 Drain-source breakdown voltage

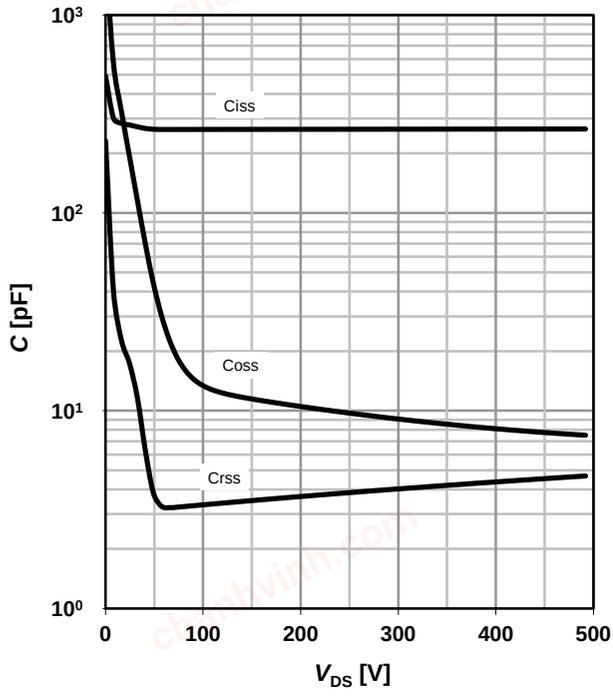
$V_{BR(DSS)}$=f(T_j); I_D=0.25 mA



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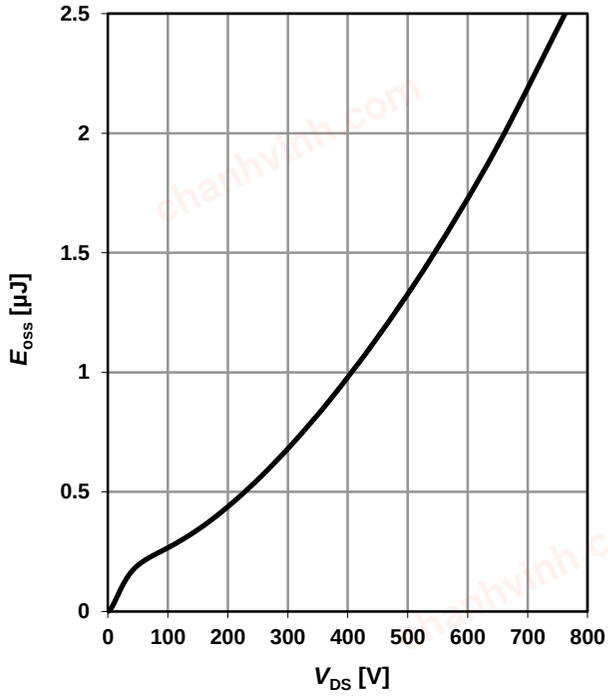
13 Typ. capacitances

C=f(V_{DS}); V_{GS}=0 V; f=1 MHz



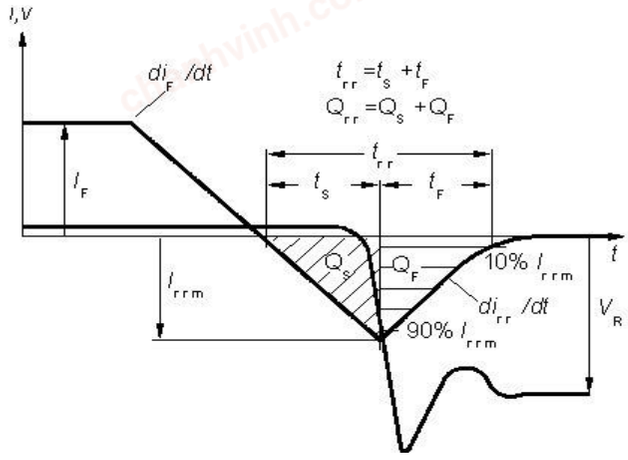
14 Typ. Coss stored energy

E_{oss}=f(V_{DS})



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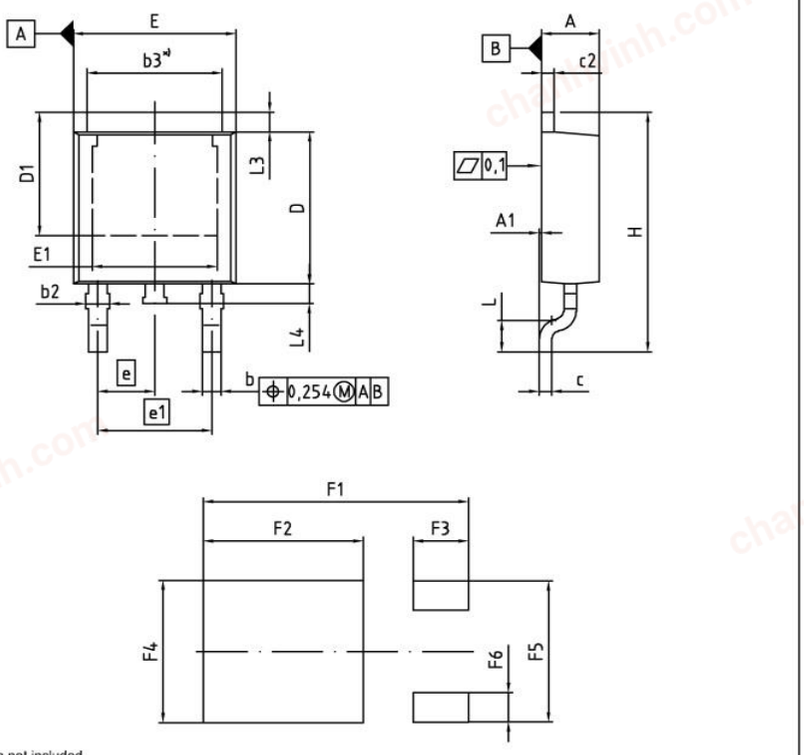
Definition of diode switching characteristics



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PG-TO252-3: Outline

TO252-3 (DPAK)



*) mold flash not included

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29 (BSC)		0.090 (BSC)	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.60		0.417	
F2	6.40		0.252	
F3	2.20		0.087	
F4	5.80		0.228	
F5	5.76		0.227	
F6	1.20		0.047	

DOCUMENT NO.
Z8B00003328

SCALE 0 2.0 0 2.0 4mm

EUROPEAN PROJECTION

ISSUE DATE
16-02-2011

REVISION
04

dimensions in mm/inches

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Revision 2013-11-21, Rev. 1.1, Final Data Sheet

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Edition 2011-09-30
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81726 Munich, Germany
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